18-Mbit (512K x 36/1M x 18) Flow-Through SRAM

Features

- Supports 133 MHz bus operations
- 512K x 36/1M x 18 common IO
- 2.5V core power supply (V_{DD})
- 2.5V IO supply (V_{DDQ})
- Fast clock-to-output times, 6.5 ns (133 MHz version)
- Provides high-performance 2-1-1-1 access rate
- User selectable burst counter supporting Intel® Pentium® interleaved or linear burst sequences
- Separate processor and controller address strobes
- Synchronous self timed write
- Asynchronous output enable
- CY7C1381DV25/CY7C1383DV25 available in JEDEC-standard Pb-free 100-pin TQFP, Pb-free and non Pb-free 165-ball FBGA package. CY7C1381FV25/CY7C1383FV25 available in Pb-free and non Pb-free 119-ball BGA package
- IEEE 1149.1 JTAG-Compatible Boundary Scan
- ZZ sleep mode option

Functional Description [1]

The CY7C1381DV25/CY7C1383DV25/CY7C1381FV25/CY7C1383FV25 is a 2.5V, 512K x 36 and 1M x 18 synchronous flow through SRAMs, designed to interface with high-speed microprocessors with minimum glue logic. Maximum access delay from clock rise is 6.5 ns (133 MHz version). A 2-bit on-chip counter captures the first address in a burst and increments the address automatically for the rest of the burst access. All synchronous inputs are gated by registers controlled by a positive edge triggered clock input (CLK). The synchronous inputs include all addresses, all data inputs, address pipelining chip enable ($\overline{CE}_1$), depth expansion chip enables (CE_2 and $\overline{CE}_3$ [2]), burst control inputs ($\overline{ADSC}$, $\overline{ADSP}$, and $\overline{ADV}$), write enables ($\overline{BW}_x$, and $\overline{BWE}$), and global write ($\overline{GW}$). Asynchronous inputs include the output enable ($\overline{OE}$) and the ZZ pin.

The CY7C1381DV25/CY7C1383DV25/CY7C1381FV25/CY7C1383FV25 allows interleaved or linear burst sequences, selected by the MODE input pin. A HIGH selects an interleaved burst sequence, while a LOW selects a linear burst sequence. Burst accesses can be initiated with the processor address strobe ($\overline{ADSP}$) or the cache controller address strobe ($\overline{ADSC}$) inputs. Address advancement is controlled by the address advancement ($\overline{ADV}$) input.

Addresses and chip enables are registered at rising edge of clock when either address strobe processor ($\overline{ADSP}$) or address strobe controller ($\overline{ADSC}$) are active. Subsequent burst addresses can be internally generated as controlled by the advance pin ($\overline{ADV}$).

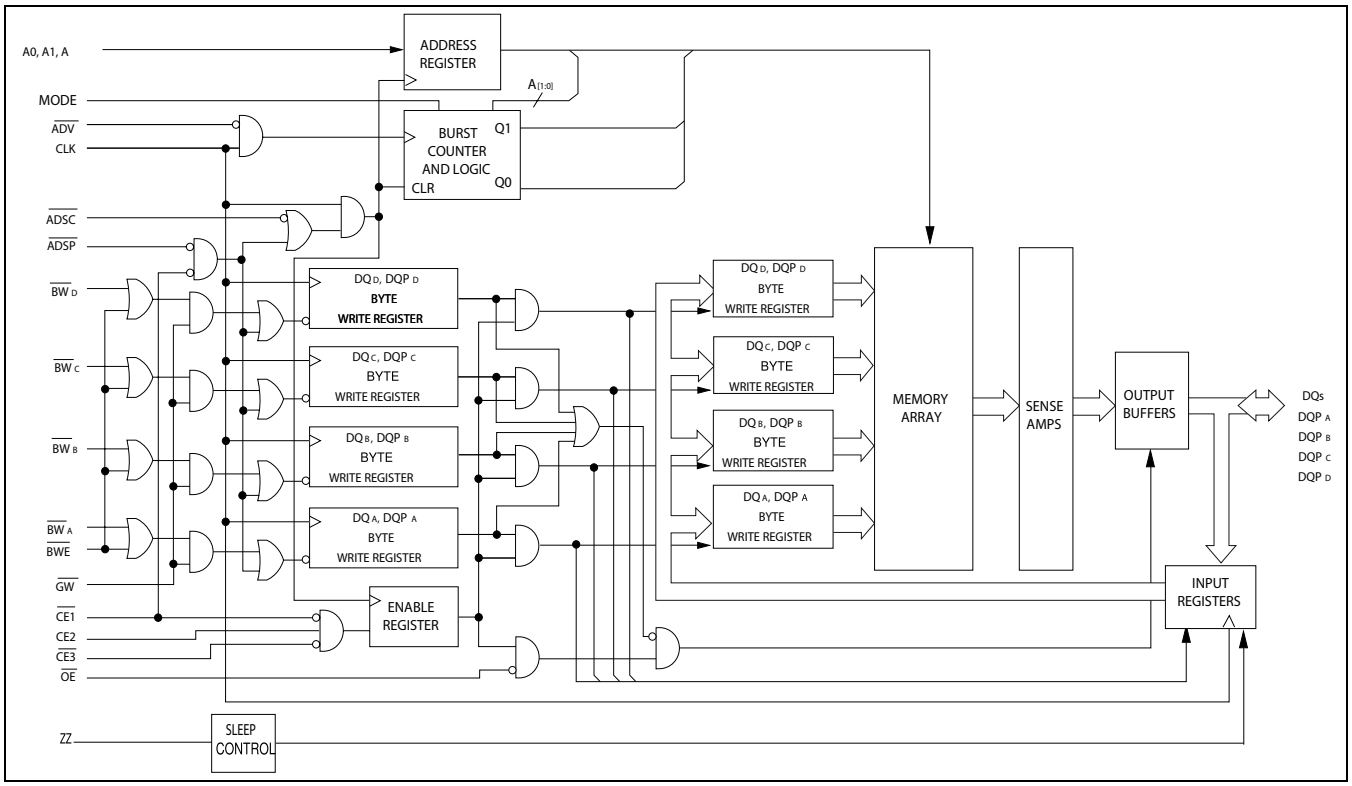
The CY7C1381DV25/CY7C1383DV25/CY7C1381FV25/CY7C1383FV25 operates from a +2.5V core power supply while all outputs also operate with a +2.5 supply. All inputs and outputs are JEDEC-standard and JESD8-5-compatible.

Selection Guide

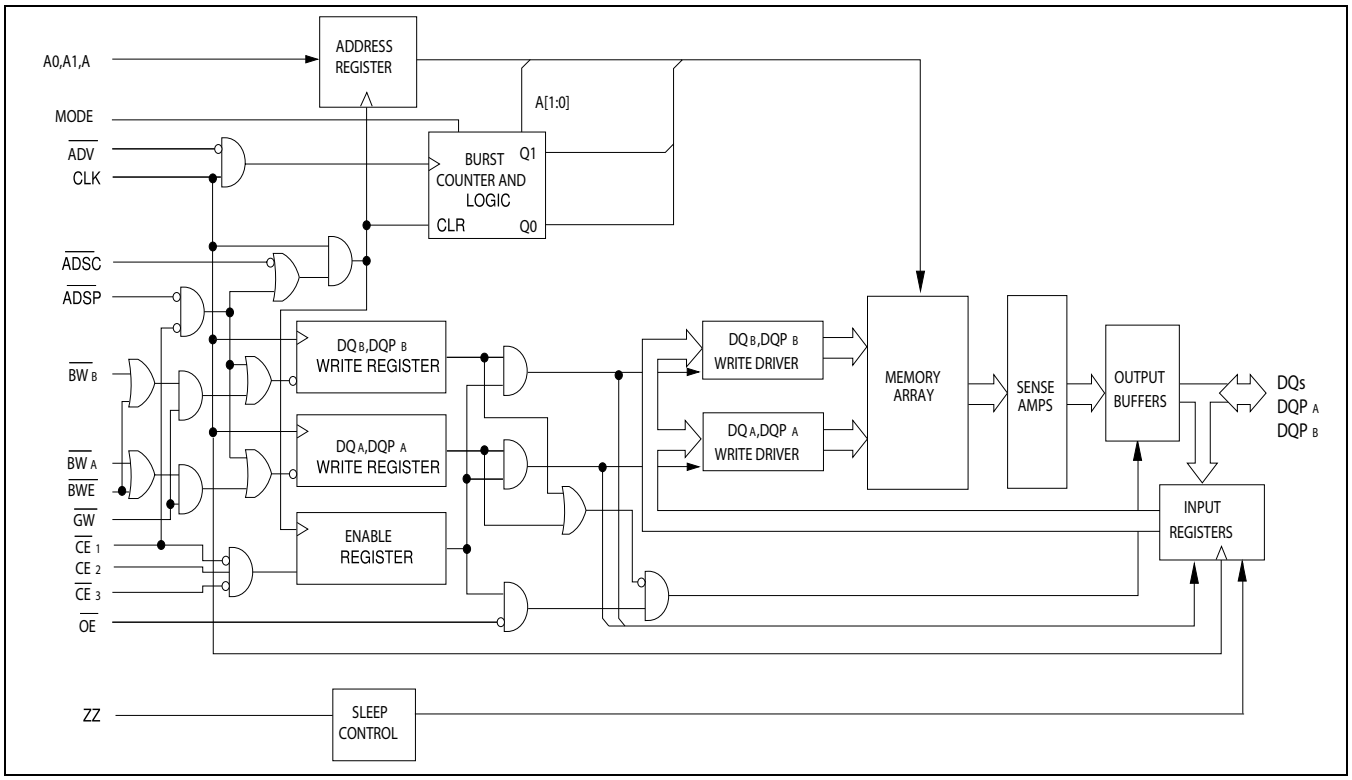
	133 MHz	100 MHz	Unit
Maximum Access Time	6.5	8.5	ns
Maximum Operating Current	210	175	mA
Maximum CMOS Standby Current	70	70	mA

Notes
1. For best practices or recommendations, please refer to the Cypress application note AN1064, *SRAM System Design Guidelines* on www.cypress.com.
2. $\overline{CE}_3$, CE_2 are for TQFP and 165 FBGA package only. 119 BGA is offered only in 1 chip enable.

Logic Block Diagram – CY7C1381DV25/CY7C1381FV25 [3] (512K x 36)



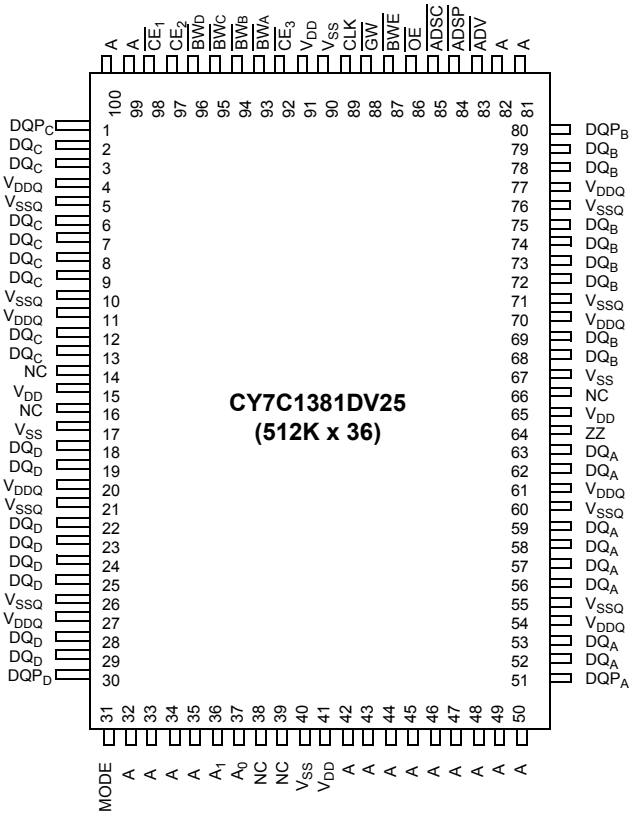
Logic Block Diagram – CY7C1383DV25/CY7C1383FV25 [3] (1M x 18)

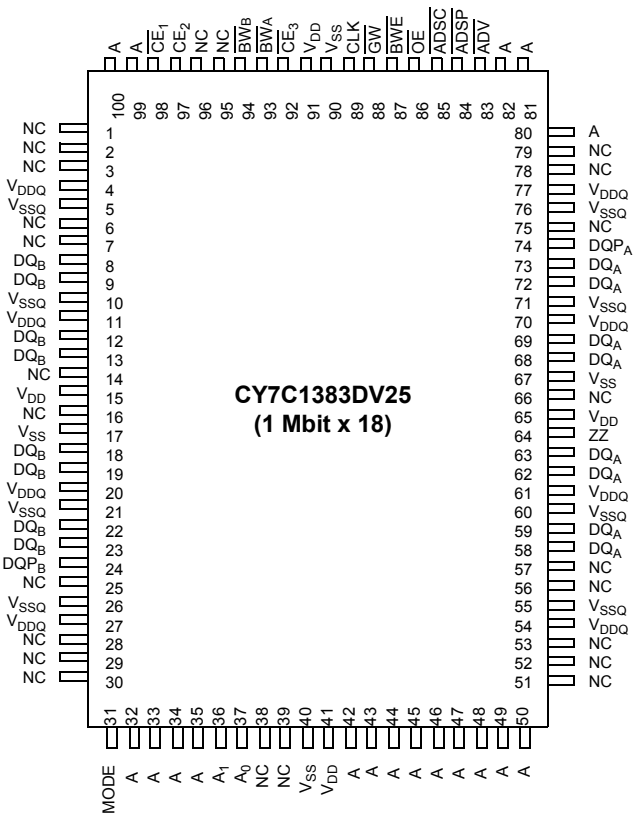


Note
3. CY7C1381FV25 and CY7C1383FV25 have only 1 chip enable ($\overline{CE}_1$).

Pin Configurations

100-pin TQFP Pinout (3 Chip Enable)





Pin Configurations (continued)

119-Ball BGA Pinout

CY7C1381FV25 (512K x 36)

	1	2	3	4	5	6	7
A	V_{DDQ}	A	A	$\overline{ADSP}$	A	A	V_{DDQ}
B	NC/288M	A	A	$\overline{ADSC}$	A	A	NC/576M
C	NC/144M	A	A	V_{DD}	A	A	NC/1G
D	DQ_C	DQP_C	V_{SS}	NC	V_{SS}	DQP_B	DQ_B
E	DQ_C	DQ_C	V_{SS}	$\overline{CE_1}$	V_{SS}	DQ_B	DQ_B
F	V_{DDQ}	DQ_C	V_{SS}	$\overline{OE}$	V_{SS}	DQ_B	V_{DDQ}
G	DQ_C	DQ_C	$\overline{BW_C}$	$\overline{ADV}$	$\overline{BW_B}$	DQ_B	DQ_B
H	DQ_C	DQ_C	V_{SS}	$\overline{GW}$	V_{SS}	DQ_B	DQ_B
J	V_{DDQ}	V_{DD}	NC	V_{DD}	NC	V_{DD}	V_{DDQ}
K	DQ_D	DQ_D	V_{SS}	CLK	V_{SS}	DQ_A	DQ_A
L	DQ_D	DQ_D	$\overline{BW_D}$	NC	$\overline{BW_A}$	DQ_A	DQ_A
M	V_{DDQ}	DQ_D	V_{SS}	$\overline{BWE}$	V_{SS}	DQ_A	V_{DDQ}
N	DQ_D	DQ_D	V_{SS}	A1	V_{SS}	DQ_A	DQ_A
P	DQ_D	DQP_D	V_{SS}	A0	V_{SS}	DQP_A	DQ_A
R	NC	A	MODE	V_{DD}	NC	A	NC
T	NC	NC/72M	A	A	A	NC/36M	ZZ
U	V_{DDQ}	TMS	TDI	TCK	TDO	NC	V_{DDQ}

CY7C1383FV25 (1M x 18)

	1	2	3	4	5	6	7
A	V_{DDQ}	A	A	$\overline{ADSP}$	A	A	V_{DDQ}
B	NC/288M	A	A	$\overline{ADSC}$	A	A	NC/576M
C	NC/144M	A	A	V_{DD}	A	A	NC/1G
D	DQ_B	NC	V_{SS}	NC	V_{SS}	DQP_A	NC
E	NC	DQ_B	V_{SS}	$\overline{CE_1}$	V_{SS}	NC	DQ_A
F	V_{DDQ}	NC	V_{SS}	$\overline{OE}$	V_{SS}	DQ_A	V_{DDQ}
G	NC	DQ_B	$\overline{BW_B}$	$\overline{ADV}$	NC	NC	DQ_A
H	DQ_B	NC	V_{SS}	$\overline{GW}$	V_{SS}	DQ_A	NC
J	V_{DDQ}	V_{DD}	NC	V_{DD}	NC	V_{DD}	V_{DDQ}
K	NC	DQ_B	V_{SS}	CLK	V_{SS}	NC	DQ_A
L	DQ_B	NC	NC	NC	$\overline{BW_A}$	DQ_A	NC
M	V_{DDQ}	DQ_B	V_{SS}	$\overline{BWE}$	V_{SS}	NC	V_{DDQ}
N	DQ_B	NC	V_{SS}	A1	V_{SS}	DQ_A	NC
P	NC	DQP_B	V_{SS}	A0	V_{SS}	NC	DQ_A
R	NC	A	MODE	V_{DD}	NC	A	NC
T	NC/72M	A	A	NC/36M	A	A	ZZ
U	V_{DDQ}	TMS	TDI	TCK	TDO	NC	V_{DDQ}

Pin Configurations (continued)

165-Ball FBGA Pinout(3 Chip Enable)

CY7C1381DV25 (512K x 36)

	1	2	3	4	5	6	7	8	9	10	11
A	NC/288M	A	$\overline{CE_1}$	$\overline{BW_C}$	$\overline{BW_B}$	$\overline{CE_3}$	$\overline{BWE}$	$\overline{ADSC}$	$\overline{ADV}$	A	NC
B	NC/144M	A	CE_2	$\overline{BW_D}$	$\overline{BW_A}$	CLK	$\overline{GW}$	$\overline{OE}$	$\overline{ADSP}$	A	NC/576M
C	DQP_C	NC	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	NC/1G	DQP_B
D	DQ_C	DQ_C	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	DQ_B	DQ_B
E	DQ_C	DQ_C	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	DQ_B	DQ_B
F	DQ_C	DQ_C	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	DQ_B	DQ_B
G	DQ_C	DQ_C	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	DQ_B	DQ_B
H	NC	NC	NC	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	NC	NC	ZZ
J	DQ_D	DQ_D	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	DQ_A	DQ_A
K	DQ_D	DQ_D	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	DQ_A	DQ_A
L	DQ_D	DQ_D	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	DQ_A	DQ_A
M	DQ_D	DQ_D	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	DQ_A	DQ_A
N	DQP_D	NC	V_{DDQ}	V_{SS}	NC	A	NC	V_{SS}	V_{DDQ}	NC	DQP_A
P	NC	NC/72M	A	A	TDI	A1	TDO	A	A	A	A
R	MODE	NC/36M	A	A	TMS	A0	TCK	A	A	A	A

CY7C1383DV25 (1Mx 18)

	1	2	3	4	5	6	7	8	9	10	11
A	NC/288M	A	$\overline{CE_1}$	$\overline{BW_B}$	NC	$\overline{CE_3}$	$\overline{BWE}$	$\overline{ADSC}$	$\overline{ADV}$	A	A
B	NC/144M	A	CE_2	NC	$\overline{BW_A}$	CLK	$\overline{GW}$	$\overline{OE}$	$\overline{ADSP}$	A	NC/576M
C	NC	NC	V_{DDQ}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{SS}	V_{DDQ}	NC/1G	DQP_A
D	NC	DQ_B	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	NC	DQ_A
E	NC	DQ_B	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	NC	DQ_A
F	NC	DQ_B	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	NC	DQ_A
G	NC	DQ_B	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	NC	DQ_A
H	V_{SS}	NC	NC	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	NC	NC	ZZ
J	DQ_B	NC	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	DQ_A	NC
K	DQ_B	NC	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	DQ_A	NC
L	DQ_B	NC	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	DQ_A	NC
M	DQ_B	NC	V_{DDQ}	V_{DD}	V_{SS}	V_{SS}	V_{SS}	V_{DD}	V_{DDQ}	DQ_A	NC
N	DQP_B	NC	V_{DDQ}	V_{SS}	NC	A	NC	V_{SS}	V_{DDQ}	NC	NC
P	NC	NC/72M	A	A	TDI	A1	TDO	A	A	A	A
R	MODE	NC/36M	A	A	TMS	A0	TCK	A	A	A	A

Pin Definitions

Name	IO	Description
A_0, A_1, A	Input-Synchronous	**Address inputs used to select one of the address locations**. Sampled at the rising edge of the CLK if $\overline{ADSP}$ or $\overline{ADSC}$ is active LOW, and $\overline{CE}_1$, CE_2, and $\overline{CE}_3$ [2] are sampled active. $A_{[1:0]}$ feed the 2-bit counter.
$\overline{BW}_A$, $\overline{BW}_B$ $\overline{BW}_C$, $\overline{BW}_D$	Input-Synchronous	**Byte write select inputs, active LOW**. Qualified with $\overline{BWE}$ to conduct byte writes to the SRAM. Sampled on the rising edge of CLK.
$\overline{GW}$	Input-Synchronous	**Global write enable input, active LOW**. When asserted LOW on the rising edge of CLK, a global write is conducted (all bytes are written, regardless of the values on $\overline{BW}_{[A:D]}$ and $\overline{BWE}$).
CLK	Input-Clock	**Clock input**. Used to capture all synchronous inputs to the device. Also used to increment the burst counter when $\overline{ADV}$ is asserted LOW, during a burst operation.
$\overline{CE}_1$	Input-Synchronous	**Chip enable 1 input, active LOW**. Sampled on the rising edge of CLK. Used in conjunction with CE_2 and $\overline{CE}_3$ [2] to select or deselect the device. $\overline{ADSP}$ is ignored if $\overline{CE}_1$ is HIGH. $\overline{CE}_1$ is sampled only when a new external address is loaded.
CE_2	Input-Synchronous	**Chip enable 2 input, active HIGH**. Sampled on the rising edge of CLK. Used in conjunction with $\overline{CE}_1$ and $\overline{CE}_3$ [2] to select or deselect the device. CE_2 is sampled only when a new external address is loaded.
$\overline{CE}_3$ [2]	Input-Synchronous	**Chip enable 3 input, active LOW**. Sampled on the rising edge of CLK. Used in conjunction with $\overline{CE}_1$ and $\overline{CE}_2$ to select or deselect the device. $\overline{CE}_3$ is sampled only when a new external address is loaded.
$\overline{OE}$	Input-Asynchronous	**Output enable, asynchronous input, active LOW**. Controls the direction of the IO pins. When LOW, the IO pins behave as outputs. When deasserted HIGH, IO pins are tri-stated, and act as input data pins. $\overline{OE}$ is masked during the first clock of a read cycle when emerging from a deselected state.
$\overline{ADV}$	Input-Synchronous	**Advance input signal.** Sampled on the rising edge of CLK. When asserted, it automatically increments the address in a burst cycle.
$\overline{ADSP}$	Input-Synchronous	**Address strobe from processor, sampled on the rising edge of CLK, active LOW**. When asserted LOW, addresses presented to the device are captured in the address registers. $A_{[1:0]}$ are also loaded into the burst counter. When $\overline{ADSP}$ and $\overline{ADSC}$ are both asserted, only $\overline{ADSP}$ is recognized. $\overline{ASDP}$ is ignored when $\overline{CE}_1$ is deasserted HIGH.
$\overline{ADSC}$	Input-Synchronous	**Address strobe from controller, sampled on the rising edge of CLK, active LOW**. When asserted LOW, addresses presented to the device are captured in the address registers. $A_{[1:0]}$ are also loaded into the burst counter. When $\overline{ADSP}$ and $\overline{ADSC}$ are both asserted, only $\overline{ADSP}$ is recognized·
$\overline{BWE}$	Input-Synchronous	**Byte write enable input, active LOW**. Sampled on the rising edge of CLK. This signal must be asserted LOW to conduct a byte write.
ZZ	Input-Asynchronous	**ZZ sleep input**. This active HIGH input places the device in a non-time critical sleep condition with data integrity preserved. For normal operation, this pin has to be LOW or left floating. ZZ pin has an internal pull down.
DQ_s	IO-Synchronous	**Bidirectional data IO lines**. As inputs, they feed into an on-chip data register that is triggered by the rising edge of CLK. As outputs, they deliver the data contained in the memory location specified by the addresses presented during the previous clock rise of the read cycle. The direction of the pins is controlled by $\overline{OE}$. When $\overline{OE}$ is asserted LOW, the pins behave as outputs. When HIGH, DQ_s and DQP_X are placed in a tri-state condition.The outputs are automatically tri-stated during the data portion of a write sequence, during the first clock when emerging from a deselected state, and when the device is deselected, regardless of the state of $\overline{OE}$.
DQP_X	IO-Synchronous	**Bidirectional data parity IO lines.** Functionally, these signals are identical to DQ_s. During write sequences, DQP_X is controlled by $\overline{BW}_X$ correspondingly.

Pin Definitions (continued)

Name	IO	Description
MODE	Input-Static	**Selects burst order**. When tied to GND selects linear burst sequence. When tied to V_{DD} or left floating selects interleaved burst sequence. This is a strap pin and must remain static during device operation. Mode pin has an internal pull up.
V_{DD}	Power Supply	**Power supply inputs to the core of the device**.
V_{DDQ}	IO Power Supply	**Power supply for the IO circuitry**.
V_{SS}	Ground	**Ground for the core of the device**.
V_{SSQ}	IO Ground	**Ground for the IO circuitry**.
TDO	JTAG serial output Synchronous	**Serial data-out to the JTAG circuit**. Delivers data on the negative edge of TCK. If the JTAG feature is not used, this pin can be left unconnected. This pin is not available on TQFP packages.
TDI	JTAG serial input Synchronous	**Serial data-in to the JTAG circuit**. Sampled on the rising edge of TCK. If the JTAG feature is not used, this pin can be left floating or connected to V_{DD} through a pull up resistor. This pin is not available on TQFP packages.
TMS	JTAG serial input Synchronous	**Serial data-in to the JTAG circuit**. Sampled on the rising edge of TCK. If the JTAG feature is not used, this pin can be disconnected or connected to V_{DD}. This pin is not available on TQFP packages.
TCK	JTAG-Clock	**Clock input to the JTAG circuitry**. If the JTAG feature is not used, this pin must be connected to V_{SS}. This pin is not available on TQFP packages.
NC, NC/(36M, 72M, 144M, 288M, 576M, 1G)	-	**No Connects**. Not internally connected to the die. 36M, 72M, 144M, 288M, 576M, and 1G are address expansion pins and are not internally connected to the die.
V_{SS}/DNU	Ground/DNU	This pin can be connected to ground or can be left floating.

Functional Overview

All synchronous inputs pass through input registers controlled by the rising edge of the clock. Maximum access delay from the clock rise (t_{CDV}) is 6.5 ns (133 MHz device).

The CY7C1381DV25/CY7C1383DV25/CY7C1381FV25/CY7C1383FV25 supports secondary cache in systems using a linear or interleaved burst sequence. The interleaved burst order supports Pentium® and i486™ processors. The linear burst sequence is suited for processors that use a linear burst sequence. The burst order is user selectable, and is determined by sampling the MODE input. Accesses can be initiated with either the processor address strobe ($\overline{ADSP}$) or the controller address strobe ($\overline{ADSC}$). Address advancement through the burst sequence is controlled by the $\overline{ADV}$ input. A two-bit on-chip wraparound burst counter captures the first address in a burst sequence and automatically increments the address for the rest of the burst access.

Byte write operations are qualified with the byte write enable ($\overline{BWE}$) and byte write select ($\overline{BW_X}$) inputs. A global write enable (GW) overrides all byte write inputs and writes data to all four bytes. All writes are simplified with on-chip synchronous self timed write circuitry.

Three synchronous chip selects ($\overline{CE_1}$, CE_2, $\overline{CE_3}$ [2]) and an asynchronous output enable ($\overline{OE}$) provide for easy bank selection and output tri-state control. $\overline{ADSP}$ is ignored if $\overline{CE_1}$ is HIGH.

Single Read Accesses

A single read access is initiated when the following conditions are satisfied at clock rise: (1) $\overline{CE_1}$, CE_2, and $\overline{CE_3}$ [2] are all asserted active, and (2) $\overline{ADSP}$ or $\overline{ADSC}$ is asserted LOW (if the access is initiated by $\overline{ADSC}$, the write inputs must be deserted during this first cycle). The address presented to the address inputs is latched into the address register and the burst counter and/or control logic, and presented to the memory core. If the $\overline{OE}$ input is asserted LOW, the requested data will be available at the data outputs with a maximum to t_{CDV} after clock rise. $\overline{ADSP}$ is ignored if $\overline{CE_1}$ is HIGH.

Single Write Accesses Initiated by $\overline{ADSP}$

This access is initiated when the following conditions are satisfied at clock rise: (1) $\overline{CE_1}$, CE_2, $\overline{CE_3}$ [2] are all asserted active, and (2) $\overline{ADSP}$ is asserted LOW. The addresses presented are loaded into the address register and the burst inputs ($\overline{GW}$, $\overline{BWE}$, and $\overline{BWX}$) are ignored during this first clock cycle. If the write inputs are asserted active (see Truth Table for Read/Write [4, 9] on page 10 for appropriate states that indicate a write) on the next clock rise, the appropriate data will be latched and written into the device. Byte writes are allowed. All IOs are tri-stated during a byte write. As this is a common IO device, the asynchronous $\overline{OE}$ input signal must be deserted

and the IOs must be tri-stated prior to the presentation of data to DQs. As a safety precaution, the data lines are tri-stated once a write cycle is detected, regardless of the state of $\overline{OE}$.

Single Write Accesses Initiated by $\overline{ADSC}$

This write access is initiated when the following conditions are satisfied at clock rise: (1) $\overline{CE}_1$, CE_2, and $\overline{CE}_3$ [2] are all asserted active, (2) $\overline{ADSC}$ is asserted LOW, (3) $\overline{ADSP}$ is deserted HIGH, and (4) the write input signals ($\overline{GW}$, $\overline{BWE}$, and $\overline{BW}_X$) indicate a write access. $\overline{ADSC}$ is ignored if $\overline{ADSP}$ is active LOW.

The addresses presented are loaded into the address register and the burst counter, the control logic, or both, and delivered to the memory core. The information presented to DQ_X will be written into the specified address location. Byte writes are allowed. All IOs are tri-stated when a write is detected, even a byte write. Since this is a common IO device, the asynchronous $\overline{OE}$ input signal must be deasserted and the IOs must be tri-stated prior to the presentation of data to DQs. As a safety precaution, the data lines are tri-stated once a write cycle is detected, regardless of the state of $\overline{OE}$.

Burst Sequences

The CY7C1381DV25/CY7C1383DV25/CY7C1381FV25/CY7C1383FV25 provides an on-chip two-bit wraparound burst counter inside the SRAM. The burst counter is fed by $A_{[1:0]}$, and can follow either a linear or interleaved burst order. The burst order is determined by the state of the MODE input. A LOW on MODE will select a linear burst sequence. A HIGH on MODE will select an interleaved burst order. Leaving MODE unconnected will cause the device to default to a interleaved burst sequence.

Sleep Mode

The ZZ input pin is an asynchronous input. Asserting ZZ places the SRAM in a power conservation sleep mode. Two clock cycles are required to enter into or exit from this sleep mode. While in this mode, data integrity is guaranteed. Accesses pending when entering the sleep mode are not considered valid nor is the completion of the operation guaranteed. The device must be deselected prior to entering the sleep mode. $\overline{CE}_1$, CE_2, $\overline{CE}_3$ [2], $\overline{ADSP}$, and $\overline{ADSC}$ must remain inactive for the duration of t_{ZZREC} after the ZZ input returns LOW.

Interleaved Burst Address Table (MODE = Floating or V_{DD})

First Address A1: A0	Second Address A1: A0	Third Address A1: A0	Fourth Address A1: A0
00	01	10	11
01	00	11	10
10	11	00	01
11	10	01	00

Linear Burst Address Table (MODE = GND)

First Address A1: A0	Second Address A1: A0	Third Address A1: A0	Fourth Address A1: A0
00	01	10	11
01	10	11	00
10	11	00	01
11	00	01	10

ZZ Mode Electrical Characteristics

Parameter	Description	Test Conditions	Min.	Max.	Unit
I_{DDZZ}	Sleep mode standby current	$ZZ \geq V_{DD} - 0.2V$		80	mA
t_{ZZS}	Device operation to ZZ	$ZZ \geq V_{DD} - 0.2V$		$2t_{CYC}$	ns
t_{ZZREC}	ZZ recovery time	$ZZ \leq 0.2V$	$2t_{CYC}$		ns
t_{ZZI}	ZZ active to sleep current	This parameter is sampled		$2t_{CYC}$	ns
t_{RZZI}	ZZ Inactive to exit sleep current	This parameter is sampled	0		ns

Truth Table [4, 5, 6, 7, 8]

Cycle Description	Address Used	$\overline{CE_1}$	CE_2	$\overline{CE_3}$	ZZ	$\overline{ADSP}$	$\overline{ADSC}$	$\overline{ADV}$	$\overline{WRITE}$	$\overline{OE}$	CLK	DQ
Deselected Cycle, Power Down	None	H	X	X	L	X	L	X	X	X	L-H	Tri-State
Deselected Cycle, Power Down	None	L	L	X	L	L	X	X	X	X	L-H	Tri-State
Deselected Cycle, Power Down	None	L	X	H	L	L	X	X	X	X	L-H	Tri-State
Deselected Cycle, Power Down	None	L	L	X	L	H	L	X	X	X	L-H	Tri-State
Deselected Cycle, Power Down	None	X	X	X	L	H	L	X	X	X	L-H	Tri-State
Sleep Mode, Power Down	None	X	X	X	H	X	X	X	X	X	X	Tri-State
Read Cycle, Begin Burst	External	L	H	L	L	L	X	X	X	L	L-H	Q
Read Cycle, Begin Burst	External	L	H	L	L	L	X	X	X	H	L-H	Tri-State
Write Cycle, Begin Burst	External	L	H	L	L	H	L	X	L	X	L-H	D
Read Cycle, Begin Burst	External	L	H	L	L	H	L	X	H	L	L-H	Q
Read Cycle, Begin Burst	External	L	H	L	L	H	L	X	H	H	L-H	Tri-State
Read Cycle, Continue Burst	Next	X	X	X	L	H	H	L	H	L	L-H	Q
Read Cycle, Continue Burst	Next	X	X	X	L	H	H	L	H	H	L-H	Tri-State
Read Cycle, Continue Burst	Next	H	X	X	L	X	H	L	H	L	L-H	Q
Read Cycle, Continue Burst	Next	H	X	X	L	X	H	L	H	H	L-H	Tri-State
Write Cycle, Continue Burst	Next	X	X	X	L	H	H	L	L	X	L-H	D
Write Cycle, Continue Burst	Next	H	X	X	L	X	H	L	L	X	L-H	D
Read Cycle, Suspend Burst	Current	X	X	X	L	H	H	H	H	L	L-H	Q
Read Cycle, Suspend Burst	Current	X	X	X	L	H	H	H	H	H	L-H	Tri-State
Read Cycle, Suspend Burst	Current	H	X	X	L	X	H	H	H	L	L-H	Q
Read Cycle, Suspend Burst	Current	H	X	X	L	X	H	H	H	H	L-H	Tri-State
Write Cycle, Suspend Burst	Current	X	X	X	L	H	H	H	L	X	L-H	D
Write Cycle, Suspend Burst	Current	H	X	X	L	X	H	H	L	X	L-H	D

Notes

4. X = Don't Care, H = Logic HIGH, L = Logic LOW.
5. $\overline{WRITE}$ = L when any one or more byte write enable signals, and $\overline{BWE}$ = L or $\overline{GW}$ = L. $\overline{WRITE}$ = H when all byte write enable signals, $\overline{BWE}$, $\overline{GW}$ = H.
6. The DQ pins are controlled by the current cycle and the $\overline{OE}$ signal. $\overline{OE}$ is asynchronous and is not sampled with the clock.
7. The SRAM always initiates a read cycle when $\overline{ADSP}$ is asserted, regardless of the state of $\overline{GW}$, $\overline{BWE}$, or $\overline{BW}_X$. Writes may occur only on subsequent clocks after the $\overline{ADSP}$ or with the assertion of $\overline{ADSC}$. As a result, $\overline{OE}$ must be driven HIGH prior to the start of the write cycle to allow the outputs to tri-state. $\overline{OE}$ is a don't care for the remainder of the write cycle.
8. $\overline{OE}$ is asynchronous and is not sampled with the clock rise. It is masked internally during write cycles. During a read cycle all data bits are tri-state when $\overline{OE}$ is inactive or when the device is deselected, and all data bits behave as output when $\overline{OE}$ is active (LOW).

Truth Table for Read/Write [4, 9]

Function (CY7C1381DV25/CY7C1381FV25)	$\overline{GW}$	$\overline{BWE}$	$\overline{BW_D}$	$\overline{BW_C}$	$\overline{BW_B}$	$\overline{BW_A}$
Read	H	H	X	X	X	X
Read	H	L	H	H	H	H
Write Byte A (DQ_A, DQP_A)	H	L	H	H	H	L
Write Byte B (DQ_B, DQP_B)	H	L	H	H	L	H
Write Bytes A, B (DQ_A, DQ_B, DQP_A, DQP_B)	H	L	H	H	L	L
Write Byte C (DQ_C, DQP_C)	H	L	H	L	H	H
Write Bytes C, A (DQ_C, DQ_A, DQP_C, DQP_A)	H	L	H	L	H	L
Write Bytes C, B (DQ_C, DQ_B, DQP_C, DQP_B)	H	L	H	L	L	H
Write Bytes C, B, A (DQ_C, DQ_B, DQ_A, DQP_C, DQP_B, DQP_A)	H	L	H	L	L	L
Write Byte D (DQ_D, DQP_D)	H	L	L	H	H	H
Write Bytes D, A (DQ_D, DQ_A, DQP_D, DQP_A)	H	L	L	H	H	L
Write Bytes D, B (DQ_D, DQ_A, DQP_D, DQP_A)	H	L	L	H	L	H
Write Bytes D, B, A (DQ_D, DQ_B, DQ_A, DQP_D, DQP_B, DQP_A)	H	L	L	H	L	L
Write Bytes D, B (DQ_D, DQ_B, DQP_D, DQP_B)	H	L	L	L	H	H
Write Bytes D, B, A (DQ_D, DQ_C, DQ_A, DQP_D, DQP_C, DQP_A)	H	L	L	L	H	L
Write Bytes D, C, A (DQ_D, DQ_B, DQ_A, DQP_D, DQP_B, DQP_A)	H	L	L	L	L	H
Write All Bytes	H	L	L	L	L	L
Write All Bytes	L	X	X	X	X	X

Truth Table for Read/Write [4, 9]

Function (CY7C1383DV25/CY7C1383FV25)	$\overline{GW}$	$\overline{BWE}$	$\overline{BW_B}$	$\overline{BW_A}$
Read	H	H	X	X
Read	H	L	H	H
Write Byte A – (DQ_A and DQP_A)	H	L	H	L
Write Byte B – (DQ_B and DQP_B)	H	L	L	H
Write All Bytes	H	L	L	L
Write All Bytes	L	X	X	X

Note
9. Table only lists a partial listing of the byte write combinations. Any combination of $\overline{BW_X}$ is valid. Appropriate write will be done based on which byte write is active.

IEEE 1149.1 Serial Boundary Scan (JTAG)

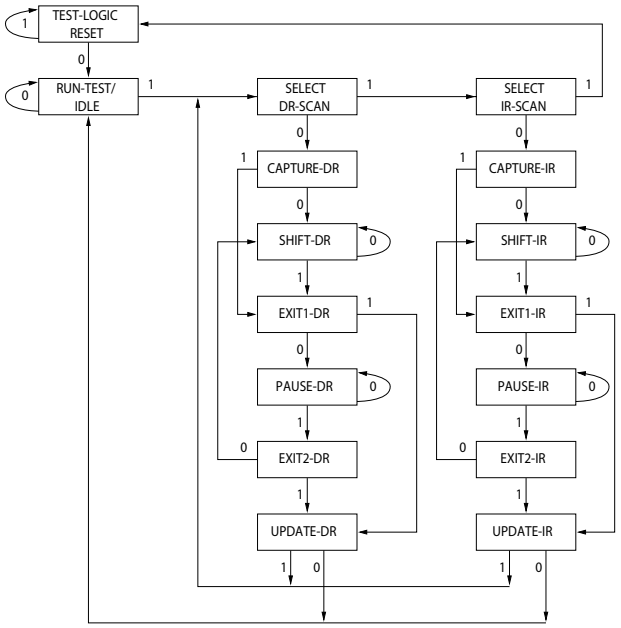
The CY7C1381DV25/CY7C1383DV25 incorporates a serial boundary scan test access port (TAP). This part is fully compliant with 1149.1. The TAP operates using JEDEC-standard 3.3V or 2.5V IO logic levels.

The CY7C1381DV25/CY7C1383DV25 contains a TAP controller, instruction register, boundary scan register, bypass register, and ID register.

Disabling the JTAG Feature

It is possible to operate the SRAM without using the JTAG feature. To disable the TAP controller, TCK must be tied LOW (V_{SS}) to prevent clocking of the device. TDI and TMS are internally pulled up and may be unconnected. They may alternately be connected to V_{DD} through a pull up resistor. TDO may be left unconnected. Upon power up, the device will come up in a reset state, which will not interfere with the operation of the device.

TAP Controller State Diagram



The 0 or 1 next to each state represents the value of TMS at the rising edge of TCK.

Test Access Port (TAP)

Test Clock (TCK)

The test clock is used only with the TAP controller. All inputs are captured on the rising edge of TCK. All outputs are driven from the falling edge of TCK.

Test MODE SELECT (TMS)

The TMS input is used to give commands to the TAP controller and is sampled on the rising edge of TCK. This pin may be left unconnected if the TAP is not used. The ball is pulled up internally, resulting in a logic HIGH level.

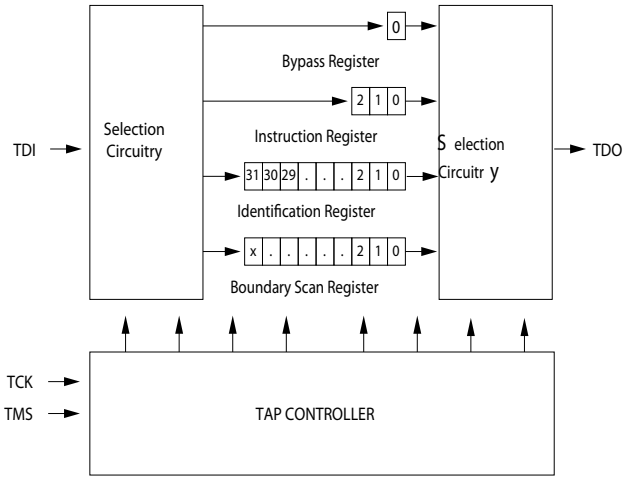
Test Data-In (TDI)

The TDI ball is used to serially input information into the registers and can be connected to the input of any of the registers. The register between TDI and TDO is chosen by the instruction that is loaded into the TAP instruction register. For information on loading the instruction register, see TAP Controller State Diagram. TDI is internally pulled up and can be unconnected if the TAP is unused in an application. TDI is connected to the most significant bit (MSB) of any register. (See TAP Controller Block Diagram).

Test Data-Out (TDO)

The TDO output ball is used to serially clock data out from the registers. The output is active depending upon the current state of the TAP state machine. The output changes on the falling edge of TCK. TDO is connected to the least significant bit (LSB) of any register. (See TAP Controller State Diagram.)

TAP Controller Block Diagram



Performing a TAP Reset

A Reset is performed by forcing TMS HIGH (V_{DD}) for five rising edges of TCK. This Reset does not affect the operation of the SRAM and may be performed while the SRAM is operating. At power up, the TAP is reset internally to ensure that TDO comes up in a High-Z state.

TAP Registers

Registers are connected between the TDI and TDO balls and allow data to be scanned in and out of the SRAM test circuitry. Only one register can be selected at a time through the instruction registers. Data is serially loaded into the TDI ball on the rising edge of TCK. Data is output on the TDO ball on the falling edge of TCK.

Instruction Register

Three-bit instructions can be serially loaded into the instruction register. This register is loaded when it is placed between the TDI and TDO balls as shown in the TAP Controller Block Diagram. Upon power up, the instruction register is loaded with the IDCODE instruction. It is also loaded with the IDCODE instruction if the controller is placed in a reset state as described in the previous section.

When the TAP controller is in the Capture-IR state, the two least significant bits are loaded with a binary ‘01’ pattern to allow for fault isolation of the board level serial test data path.

Bypass Register

To save time when serially shifting data through registers, it is sometimes advantageous to skip certain chips. The bypass register is a single-bit register that can be placed between the TDI and TDO balls. This allows data to be shifted through the SRAM with minimal delay. The bypass register is set LOW (V_{SS}) when the BYPASS instruction is executed.

Boundary Scan Register

The boundary scan register is connected to all the input and bidirectional balls on the SRAM.

The boundary scan register is loaded with the contents of the RAM IO ring when the TAP controller is in the Capture-DR state and is then placed between the TDI and TDO balls when the controller is moved to the Shift-DR state. The EXTEST, SAMPLE/PRELOAD, and SAMPLE Z instructions can be used to capture the contents of the input and output ring.

The boundary scan order tables show the order in which the bits are connected. Each bit corresponds to one of the bumps on the SRAM package. The MSB of the register is connected to TDI, and the LSB is connected to TDO.

(ID) Register

The ID register is loaded with a vendor specific 32-bit code during the Capture-DR state when the IDCODE command is loaded in the instruction register. The IDCODE is hardwired into the SRAM and can be shifted out when the TAP controller is in the Shift-DR state. The ID register has a vendor code and other information described in the Identification Register Definitions on page 14.

TAP Instruction Set

Overview

Eight different instructions are possible with the three bit instruction register. All combinations are listed in Identification Codes on page 15. Three of these instructions are listed as RESERVED and must not be used. The other five instructions are described in detail below.

Instructions are loaded into the TAP controller during the Shift-IR state, when the instruction register is placed between TDI and TDO. During this state, instructions are shifted through the instruction register through the TDI and TDO balls. To execute the instruction once it is shifted in, the TAP controller needs to be moved into the Update-IR state.

EXTEST

The EXTEST instruction enables the preloaded data to be driven out through the system output pins. This instruction also selects the boundary scan register to be connected for serial access between the TDI and TDO in the Shift-DR controller state.

IDCODE

The IDCODE instruction causes a vendor specific 32-bit code to be loaded into the instruction register. It also places the instruction register between the TDI and TDO balls and allows the IDCODE to be shifted out of the device when the TAP controller enters the Shift-DR state.

The IDCODE instruction is loaded into the instruction register upon power up or whenever the TAP controller is given a test logic reset state.

SAMPLE Z

The SAMPLE Z instruction causes the boundary scan register to be connected between the TDI and TDO balls when the TAP controller is in a Shift-DR state. The SAMPLE Z command places all SRAM outputs into a High-Z state.

SAMPLE/PRELOAD

SAMPLE/PRELOAD is a 1149.1 mandatory instruction. When the SAMPLE/PRELOAD instructions are loaded into the instruction register and the TAP controller is in the Capture-DR state, a snapshot of data on the inputs and output pins is captured in the boundary scan register.

The user must be aware that the TAP controller clock can only operate at a frequency up to 20 MHz, while the SRAM clock operates more than an order of magnitude faster. Because there is a large difference in the clock frequencies, it is possible that during the Capture-DR state, an input or output will undergo a transition. The TAP may then try to capture a signal while in transition (metastable state). This will not harm the device, but there is no guarantee as to the value that will be captured. Repeatable results may not be possible.

To guarantee that the boundary scan register will capture the correct value of a signal, the SRAM signal must be stabilized long enough to meet the TAP controller's capture setup plus hold times (t_{CS} and t_{CH}). The SRAM clock input might not be captured correctly if there is no way in a design to stop (or slow) the clock during a SAMPLE/PRELOAD instruction. If this is an issue, it is still possible to capture all other signals and simply ignore the value of the CK and $\overline{CK}$ captured in the boundary scan register.

Once the data is captured, it is possible to shift out the data by putting the TAP into the Shift-DR state. This places the boundary scan register between the TDI and TDO pins.

PRELOAD allows an initial data pattern to be placed at the latched parallel outputs of the boundary scan register cells prior to the selection of another boundary scan test operation.

The shifting of data for the SAMPLE and PRELOAD phases can occur concurrently when required; that is, while data captured is shifted out, the preloaded data is shifted in.

BYPASS

When the BYPASS instruction is loaded in the instruction register and the TAP is placed in a Shift-DR state, the bypass register is placed between the TDI and TDO balls. The advantage of the BYPASS instruction is that it shortens the boundary scan path when multiple devices are connected together on a board.

EXTEST Output Bus Tri-State

IEEE Standard 1149.1 mandates that the TAP controller be able to put the output bus into a tri-state mode.

The boundary scan register has a special bit located at bit #85 (for 119-BGA package) or bit #89 (for 165-fBGA package). When this scan cell, called the “extest output bus tri-state,” is latched into the preload register during the Update-DR state in

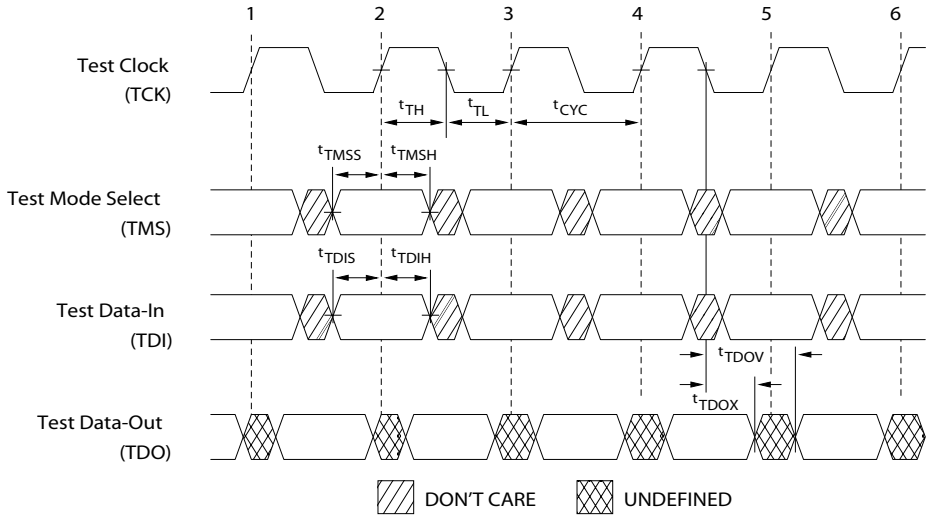
the TAP controller, it will directly control the state of the output (Q-bus) pins, when the EXTEST is entered as the current instruction. When HIGH, it will enable the output buffers to drive the output bus. When LOW, this bit will place the output bus into a High-Z condition.

This bit can be set by entering the SAMPLE/PRELOAD or EXTEST command, and then shifting the desired bit into that cell, during the Shift-DR state. During Update-DR, the value loaded into that shift-register cell will latch into the preload register. When the EXTEST instruction is entered, this bit will directly control the output Q-bus pins. Note that this bit is preset HIGH to enable the output when the device is powered up, and also when the TAP controller is in the Test-Logic-Reset state.

Reserved

These instructions are not implemented but are reserved for future use. Do not use these instructions.

TAP Timing



TAP AC Switching Characteristics

Over the Operating Range [10, 11]

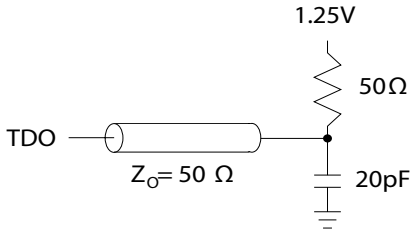
Parameter	Description	Min.	Max.	Unit
Clock				
t_{TCYC}	TCK Clock Cycle Time	50		ns
t_{TF}	TCK Clock Frequency		20	MHz
t_{TH}	TCK Clock HIGH time	20		ns
t_{TL}	TCK Clock LOW time	20		ns
Output Times				
t_{TDOV}	TCK Clock LOW to TDO Valid		10	ns
t_{TDOX}	TCK Clock LOW to TDO Invalid	0		ns
Setup Times				
t_{TMSS}	TMS Setup to TCK Clock Rise	5		ns
t_{TDIS}	TDI Setup to TCK Clock Rise	5		ns
t_{CS}	Capture Setup to TCK Rise	5		ns
Hold Times				
t_{TMSH}	TMS Hold after TCK Clock Rise	5		ns
t_{TDIH}	TDI Hold after Clock Rise	5		ns
t_{CH}	Capture Hold after Clock Rise	5		ns

Notes
10. t_{CS} and t_{CH} refer to the setup and hold time requirements of latching data from the boundary scan register.
11. Test conditions are specified using the load in TAP AC test conditions. t_R/t_F = 1 ns.

2.5V TAP AC Test Conditions

Input pulse levels ..... V_{SS} to 2.5V
Input rise and fall time..... 1 ns
Input timing reference levels..... 1.25V
Output reference levels..... 1.25V
Test load termination supply voltage..... 1.25V

2.5V TAP AC Output Load Equivalent



TAP DC Electrical Characteristics And Operating Conditions

(0°C < TA < +70°C; V_{DD} = 2.5V ±0.125V unless otherwise noted) [12]

Parameter	Description	Test Conditions		Min.	Max.	Unit
V_{OH1}	Output HIGH Voltage	I_{OH} = –1.0 mA, V_{DDQ} = 2.5V		2.0		V
V_{OH2}	Output HIGH Voltage	I_{OH} = –100 µA, V_{DDQ} = 2.5V		2.1		V
V_{OL1}	Output LOW Voltage	I_{OL} = 8.0 mA, V_{DDQ} = 2.5V			0.4	V
V_{OL2}	Output LOW Voltage	I_{OL} = 100 µA	V_{DDQ} = 2.5V		0.2	V
V_{IH}	Input HIGH Voltage		V_{DDQ} = 2.5V	1.7	V_{DD} + 0.3	V
V_{IL}	Input LOW Voltage		V_{DDQ} = 2.5V	–0.3	0.7	V
I_X	Input Load Current	GND ≤ V_{IN} ≤ V_{DDQ}		–5	5	µA

Identification Register Definitions

Instruction Field	CY7C1381DV25/ CY7C1381FV25 (512K x 36)	CY7C1383DV25/ CY7C1383FV25 (1 Mbit x 18)	Description
Revision Number (31:29)	000	000	Describes the version number
Device Depth (28:24)	01011	01011	Reserved for internal use.
Device Width (23:18) 119-BGA	101001	101001	Defines the memory type and architecture
Device Width (23:18) 165-FBGA	000001	000001	Defines the memory type and architecture
Cypress Device ID (17:12)	100101	010101	Defines the width and density
Cypress JEDEC ID Code (11:1)	00000110100	00000110100	Allows unique identification of SRAM vendor
ID Register Presence Indicator (0)	1	1	Indicates the presence of an ID register

Scan Register Sizes

Register Name	Bit Size (x36)	Bit Size (x18)
Instruction Bypass	3	3
Bypass	1	1
ID	32	32
Boundary Scan Order (119-ball BGA package)	85	85
Boundary Scan Order (165-ball FBGA package)	89	89

Note
12. All voltages referenced to V_{SS} (GND).

Identification Codes

Instruction	Code	Description
EXTEST	000	Captures IO ring contents. Places the boundary scan register between TDI and TDO. Forces all SRAM outputs to High-Z state.
IDCODE	001	Loads the ID register with the vendor ID code and places the register between TDI and TDO. This operation does not affect SRAM operations.
SAMPLE Z	010	Captures IO ring contents. Places the boundary scan register between TDI and TDO. Forces all SRAM output drivers to a High-Z state.
RESERVED	011	Do Not Use. This instruction is reserved for future use.
SAMPLE/PRELOAD	100	Captures IO ring contents. Places the boundary scan register between TDI and TDO. Does not affect SRAM operation.
RESERVED	101	Do Not Use. This instruction is reserved for future use.
RESERVED	110	Do Not Use. This instruction is reserved for future use.
BYPASS	111	Places the bypass register between TDI and TDO. This operation does not affect SRAM operations.

119-Ball BGA Boundary Scan Order [13, 14]

Bit #	Ball ID	Bit #	Ball ID	Bit #	Ball ID	Bit #	Ball ID
1	H4	23	F6	45	G4	67	L1
2	T4	24	E7	46	A4	68	M2
3	T5	25	D7	47	G3	69	N1
4	T6	26	H7	48	C3	70	P1
5	R5	27	G6	49	B2	71	K1
6	L5	28	E6	50	B3	72	L2
7	R6	29	D6	51	A3	73	N2
8	U6	30	C7	52	C2	74	P2
9	R7	31	B7	53	A2	75	R3
10	T7	32	C6	54	B1	76	T1
11	P6	33	A6	55	C1	77	R1
12	N7	34	C5	56	D2	78	T2
13	M6	35	B5	57	E1	79	L3
14	L7	36	G5	58	F2	80	R2
15	K6	37	B6	59	G1	81	T3
16	P7	38	D4	60	H2	82	L4
17	N6	39	B4	61	D1	83	N4
18	L6	40	F4	62	E2	84	P4
19	K7	41	M4	63	G2	85	Internal
20	J5	42	A5	64	H1		
21	H6	43	K4	65	J3		
22	G7	44	E4	66	2K		

Notes
13. Balls that are NC (No Connect) are preset LOW.
14. Bit #85 is preset HIGH.

165-Ball BGA Boundary Scan Order [13, 15]

Bit #	Ball ID
1	N6
2	N7
3	N10
4	P11
5	P8
6	R8
7	R9
8	P9
9	P10
10	R10
11	R11
12	H11
13	N11
14	M11
15	L11
16	K11
17	J11
18	M10
19	L10
20	K10
21	J10
22	H9
23	H10
24	G11
25	F11
26	E11
27	D11
28	G10
29	F10
30	E10

Bit #	Ball ID
31	D10
32	C11
33	A11
34	B11
35	A10
36	B10
37	A9
38	B9
39	C10
40	A8
41	B8
42	A7
43	B7
44	B6
45	A6
46	B5
47	A5
48	A4
49	B4
50	B3
51	A3
52	A2
53	B2
54	C2
55	B1
56	A1
57	C1
58	D1
59	E1
60	F1

Bit #	Ball ID
61	G1
62	D2
63	E2
64	F2
65	G2
66	H1
67	H3
68	J1
69	K1
70	L1
71	M1
72	J2
73	K2
74	L2
75	M2
76	N1
77	N2
78	P1
79	R1
80	R2
81	P3
82	R3
83	P2
84	R4
85	P4
86	N5
87	P6
88	R6
89	Internal

Note
15. Bit #89 is preset HIGH.

Maximum Ratings

Exceeding the maximum ratings may impair the useful life of the device. For user guidelines, not tested.

Storage Temperature ..... –65°C to +150°C

Ambient Temperature with Power Applied..... –55°C to +125°C

Supply Voltage on V_{DD} Relative to GND ..... –0.3V to +3.6V

Supply Voltage on V_{DDQ} Relative to GND ..... –0.3V to +V_{DD}

DC Voltage Applied to Outputs in Tri-State..... –0.5V to V_{DDQ} + 0.5V

DC Input Voltage ..... –0.5V to V_{DD} + 0.5V

Current into Outputs (LOW) ..... 20 mA

Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current ..... > 200 mA

Operating Range

Range	Ambient Temperature	V_{DD}	V_{DDQ}
Commercial	0°C to +70°C	2.5V ± 5%	2.5V – 5% to V_{DD}
Industrial	–40°C to +85°C		

Electrical Characteristics

Over the Operating Range [16, 17]

Parameter	Description	Test Conditions		Min.	Max.	Unit
V_{DD}	Power Supply Voltage			2.375	2.625	V
V_{DDQ}	IO Supply Voltage	for 2.5V IO		2.375	V_{DD}	V
V_{OH}	Output HIGH Voltage	for 2.5V IO, I_{OH} = –1.0 mA		2.0		V
V_{OL}	Output LOW Voltage	for 2.5V IO, I_{OL} = 1.0 mA			0.4	V
V_{IH}	Input HIGH Voltage [16]	for 2.5V IO		1.7	V_{DD} + 0.3V	V
V_{IL}	Input LOW Voltage [16]	for 2.5V IO		–0.3	0.7	V
I_X	Input Leakage Current except ZZ and MODE	GND ≤ V_I ≤ V_{DDQ}		–5	5	µA
	Input Current of MODE	Input = V_{SS}		–30		µA
		Input = V_{DD}			5	µA
	Input Current of ZZ	Input = V_{SS}		–5		µA
		Input = V_{DD}			30	µA
I_{OZ}	Output Leakage Current	GND ≤ V_I ≤ V_{DD}, Output Disabled		–5	5	µA
I_{DD}	V_{DD} Operating Supply Current	V_{DD} = Max., I_{OUT} = 0 mA, f = f_{MAX} = $1/t_{CYC}$	7.5-ns cycle, 133 MHz		210	mA
			10-ns cycle, 100 MHz		175	mA
I_{SB1}	Automatic CE Power Down Current—TTL Inputs	Max. V_{DD}, Device Deselected, V_{IN} ≥ V_{IH} or V_{IN} ≤ V_{IL}, f = f_{MAX}, inputs switching	7.5-ns cycle, 133 MHz		140	mA
			10-ns cycle, 100 MHz		120	
I_{SB2}	Automatic CE Power Down Current—CMOS Inputs	Max. V_{DD}, Device Deselected, V_{IN} ≥ V_{DD} – 0.3V or V_{IN} ≤ 0.3V, f = 0, inputs static	All speeds		70	mA
I_{SB3}	Automatic CE Power Down Current—CMOS Inputs	Max. V_{DD}, Device Deselected, V_{IN} ≥ V_{DDQ} – 0.3V or V_{IN} ≤ 0.3V, f = f_{MAX}, inputs switching	7.5-ns cycle, 133 MHz		130	mA
			10-ns cycle, 100 MHz		110	mA
I_{SB4}	Automatic CE Power Down Current—TTL Inputs	Max. V_{DD}, Device Deselected, V_{IN} ≥ V_{DD} – 0.3V or V_{IN} ≤ 0.3V, f = 0, inputs static	All speeds		80	mA

Notes

16. Overshoot: $V_{IH}(AC) < V_{DD}$ +1.5V (Pulse width less than $t_{CYC}/2$), undershoot: $V_{IL}(AC) > –2V$ (Pulse width less than $t_{CYC}/2$).
17. $T_{power\ up}$: assumes a linear ramp from 0V to V_{DD}(min.) within 200 ms. During this time $V_{IH} < V_{DD}$ and $V_{DDQ} \le V_{DD}$.

Capacitance [18]

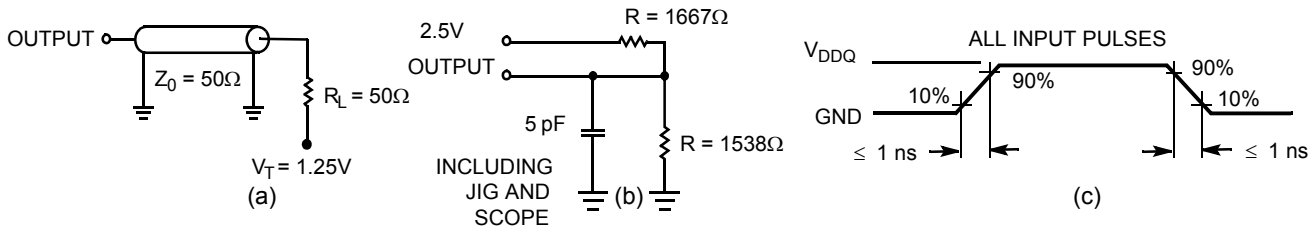
Parameter	Description	Test Conditions	100 TQFP Package	119 BGA Package	165 FBGA Package	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, V_{DD}/V_{DDQ}= 2.5V	5	8	9	pF
C_{CLK}	Clock Input Capacitance		5	8	9	pF
C_{IO}	Input/Output Capacitance		5	8	9	pF

Thermal Resistance [18]

Parameter	Description	Test Conditions	100 TQFP Package	119 BGA Package	165 FBGA Package	Unit
Θ_{JA}	Thermal Resistance (Junction to Ambient)	Test conditions follow standard test methods and procedures for measuring thermal impedance, in accordance with EIA/JESD51.	28.66	23.8	20.7	°C/W
Θ_{JC}	Thermal Resistance (Junction to Case)		4.08	6.2	4.0	°C/W

AC Test Loads and Waveforms

2.5V IO Test Load



Note
18. Tested initially and after any design or process change that may affect these parameters.

Switching Characteristics

Over the Operating Range [19, 20]

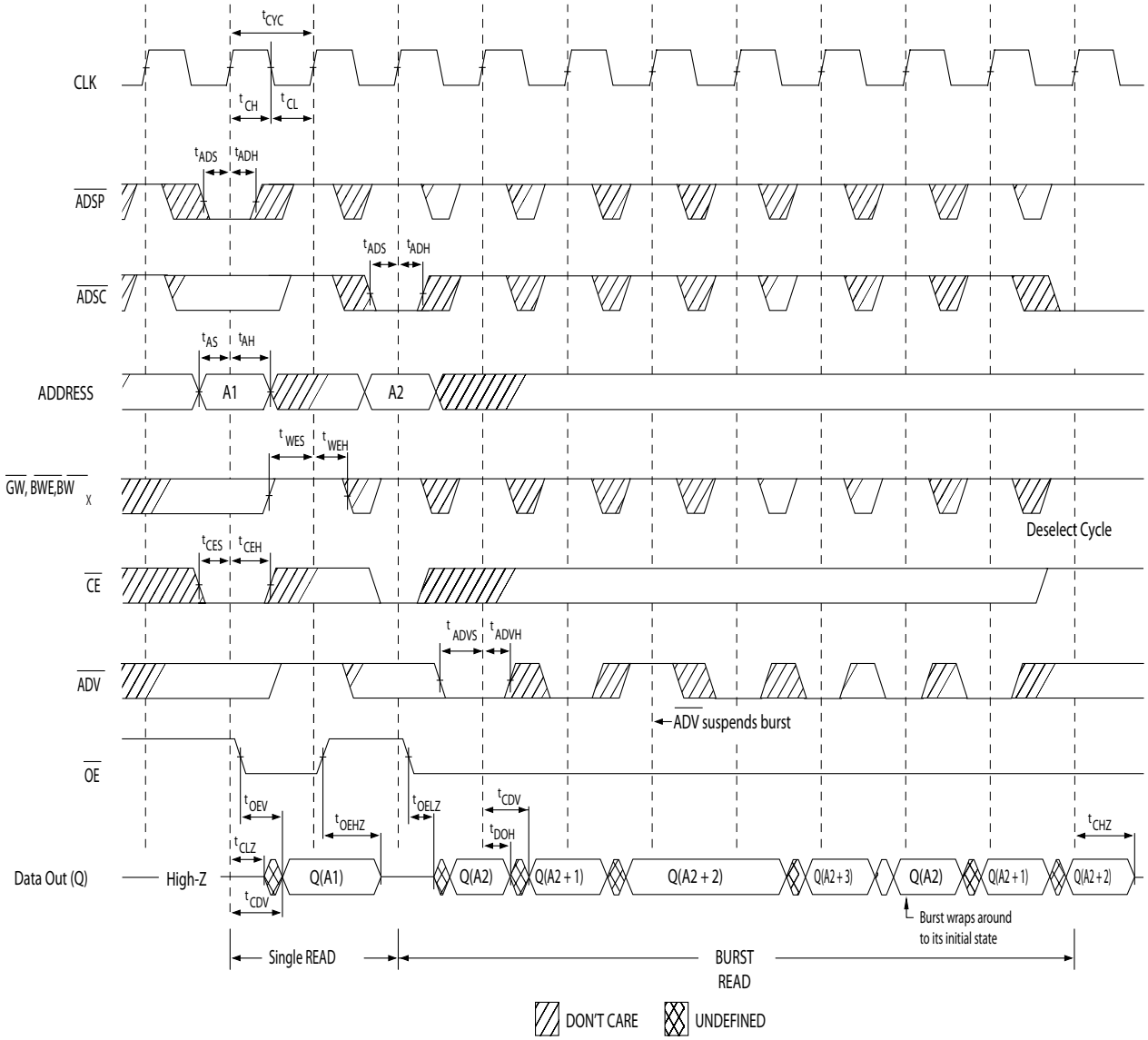
Parameter	Description	133 MHz		100 MHz		Unit
		Min.	Max.	Min.	Max.	
t_{POWER}	V_{DD}(Typical) to the first Access [21]	1		1		ms
Clock						
t_{CYC}	Clock Cycle Time	7.5		10		ns
t_{CH}	Clock HIGH	2.1		2.5		ns
t_{CL}	Clock LOW	2.1		2.5		ns
Output Times						
t_{CDV}	Data Output Valid After CLK Rise		6.5		8.5	ns
t_{DOH}	Data Output Hold After CLK Rise	2.0		2.0		ns
t_{CLZ}	Clock to Low-Z [22, 23, 24]	2.0		2.0		ns
t_{CHZ}	Clock to High-Z [22, 23, 24]	0	4.0	0	5.0	ns
t_{OEV}	$\overline{OE}$ LOW to Output Valid		3.2		3.8	ns
t_{OELZ}	$\overline{OE}$ LOW to Output Low-Z [22, 23, 24]	0		0		ns
t_{OEHZ}	$\overline{OE}$ HIGH to Output High-Z [22, 23, 24]		4.0		5.0	ns
Setup Times						
t_{AS}	Address Setup Before CLK Rise	1.5		1.5		ns
t_{ADS}	$\overline{ADSP}$, $\overline{ADSC}$ Setup Before CLK Rise	1.5		1.5		ns
t_{ADVS}	$\overline{ADV}$ Setup Before CLK Rise	1.5		1.5		ns
t_{WES}	$\overline{GW}$, $\overline{BWE}$, $\overline{BW}_{[A:D]}$ Setup Before CLK Rise	1.5		1.5		ns
t_{DS}	Data Input Setup Before CLK Rise	1.5		1.5		ns
t_{CES}	Chip Enable Setup	1.5		1.5		ns
Hold Times						
t_{AH}	Address Hold After CLK Rise	0.5		0.5		ns
t_{ADH}	$\overline{ADSP}$, $\overline{ADSC}$ Hold After CLK Rise	0.5		0.5		ns
t_{WEH}	$\overline{GW}$, $\overline{BWE}$, $\overline{BW}_{[A:D]}$ Hold After CLK Rise	0.5		0.5		ns
t_{ADVH}	$\overline{ADV}$ Hold After CLK Rise	0.5		0.5		ns
t_{DH}	Data Input Hold After CLK Rise	0.5		0.5		ns
t_{CEH}	Chip Enable Hold After CLK Rise	0.5		0.5		ns

Notes

19. Timing reference level is 1.25V.
20. Test conditions shown in (a) of AC Test Loads unless otherwise noted.
21. This part has a voltage regulator internally; t_{POWER} is the time that the power needs to be supplied above V_{DD}(minimum) initially, before a read or write operation can be initiated.
22. t_{CHZ}, t_{CLZ},t_{OELZ}, and t_{OEHZ} are specified with AC test conditions shown in part (b) of AC Test Loads. Transition is measured ± 200 mV from steady-state voltage.
23. At any given voltage and temperature, t_{OEHZ} is less than t_{OELZ} and t_{CHZ} is less than t_{CLZ} to eliminate bus contention between SRAMs when sharing the same data bus. These specifications do not imply a bus contention condition, but reflect parameters guaranteed over worst case user conditions. Device is designed to achieve High-Z prior to Low-Z under the same system conditions.
24. This parameter is sampled and not 100% tested.

Timing Diagrams

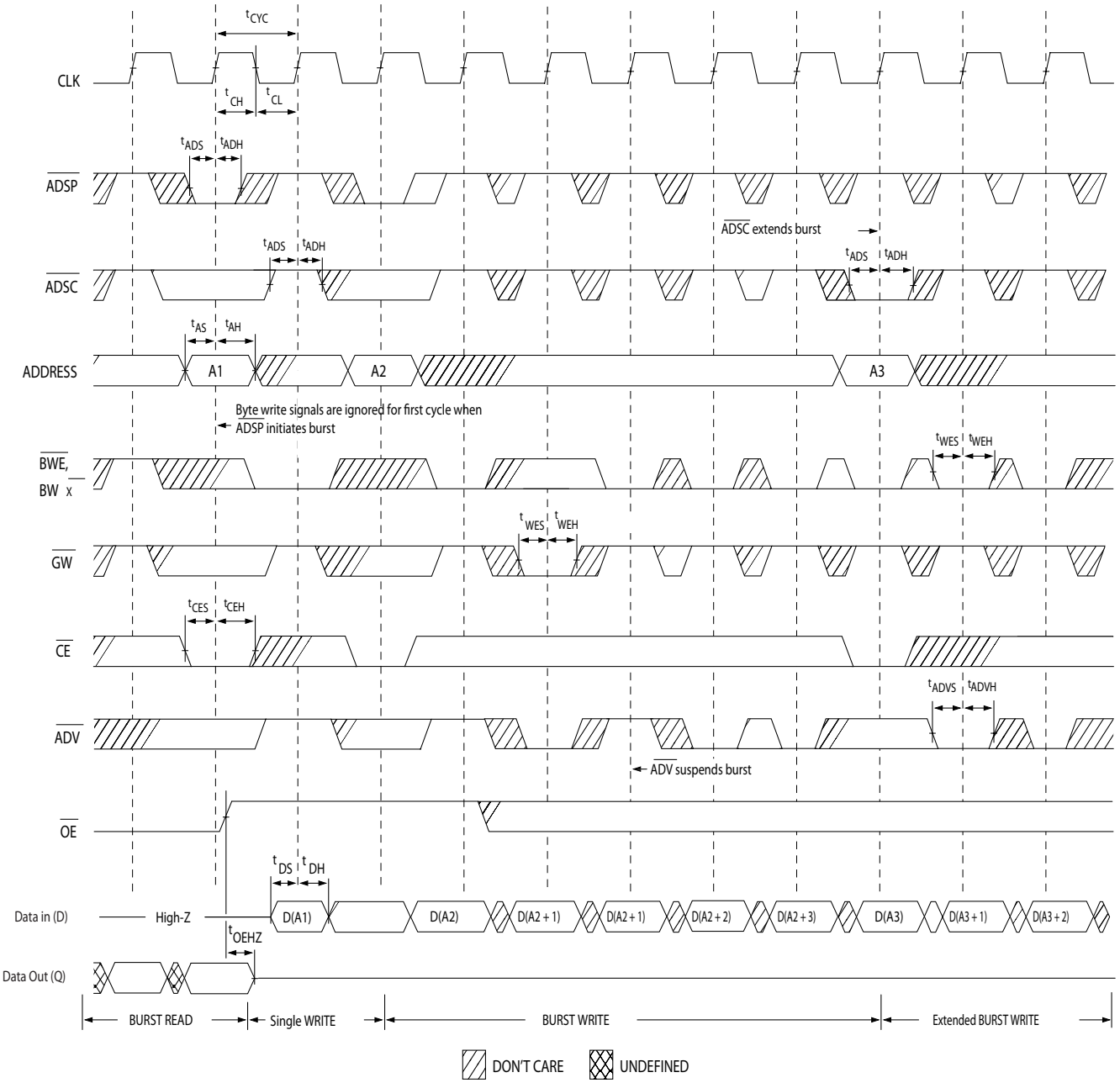
Read Cycle Timing [25]



Note
25. On this diagram, when $\overline{CE}$ is LOW: $\overline{CE}_1$ is LOW, CE_2 is HIGH and $\overline{CE}_3$ is LOW. When $\overline{CE}$ is HIGH: $\overline{CE}_1$ is HIGH or CE_2 is LOW or $\overline{CE}_3$ is HIGH.

Timing Diagrams (continued)

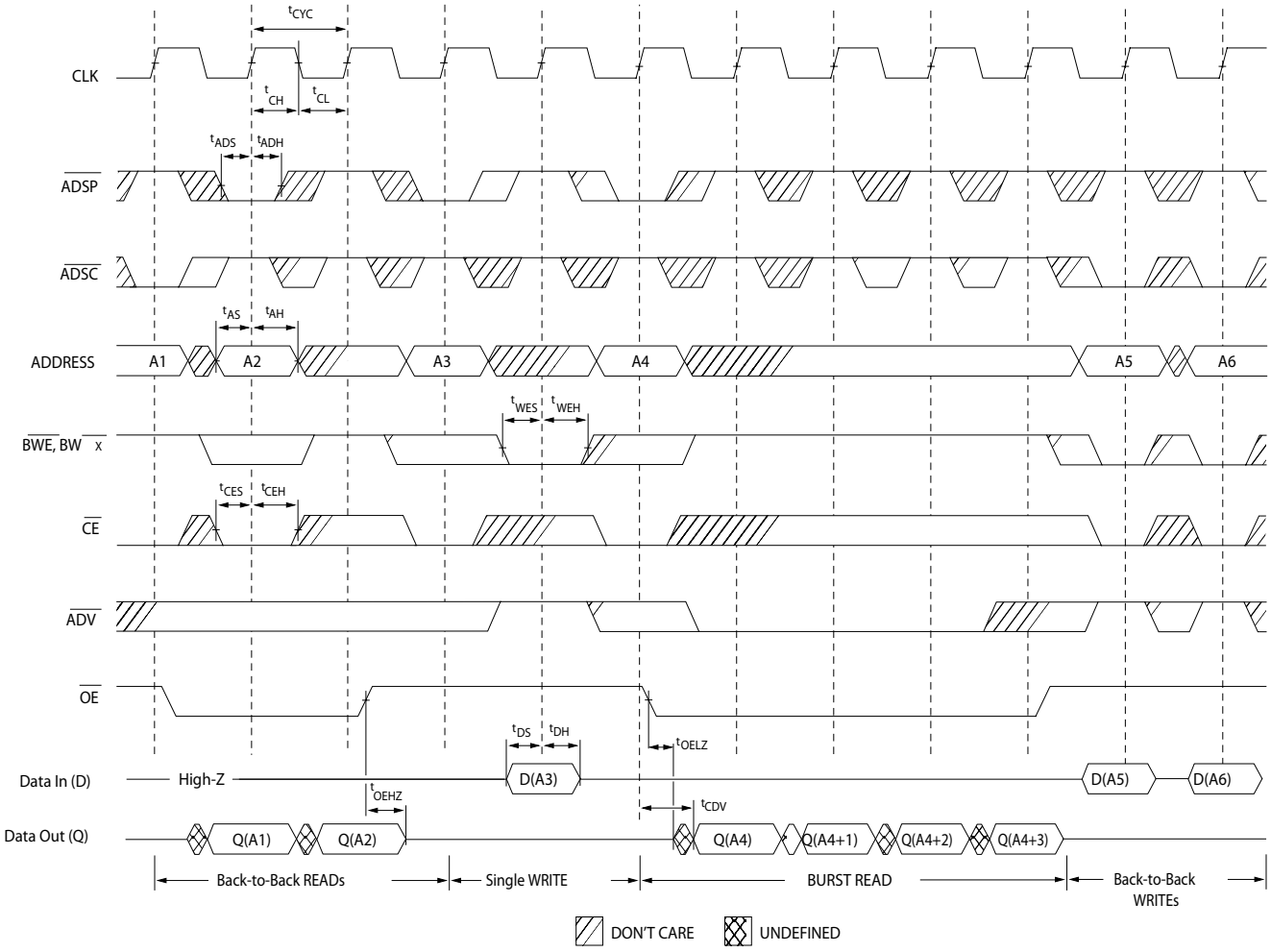
Write Cycle Timing [25, 26]



Note
26. Full width write can be initiated by either $\overline{GW}$ LOW, or by $\overline{GW}$ HIGH, $\overline{BWE}$ LOW and $\overline{BW}_X$ LOW.

Timing Diagrams (continued)

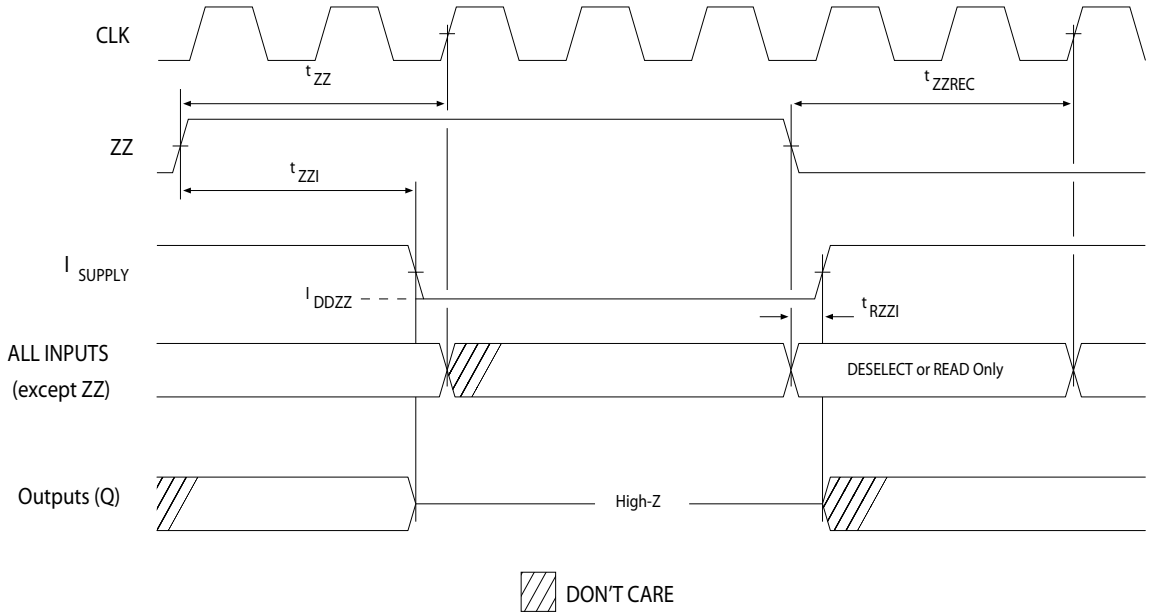
Read/Write Cycle Timing [25, 27, 28]



Notes
27. The data bus (Q) remains in high-Z following a write cycle, unless a new read access is initiated by $\overline{ADSP}$ or $\overline{ADSC}$.
28. $\overline{GW}$ is HIGH.

Timing Diagrams (continued)

ZZ Mode Timing [29, 30]



Notes
29. Device must be deselected when entering ZZ sleep mode. See Cycle Descriptions table for all possible signal conditions to deselect the device.
30. DQs are in high-Z when exiting ZZ sleep mode.

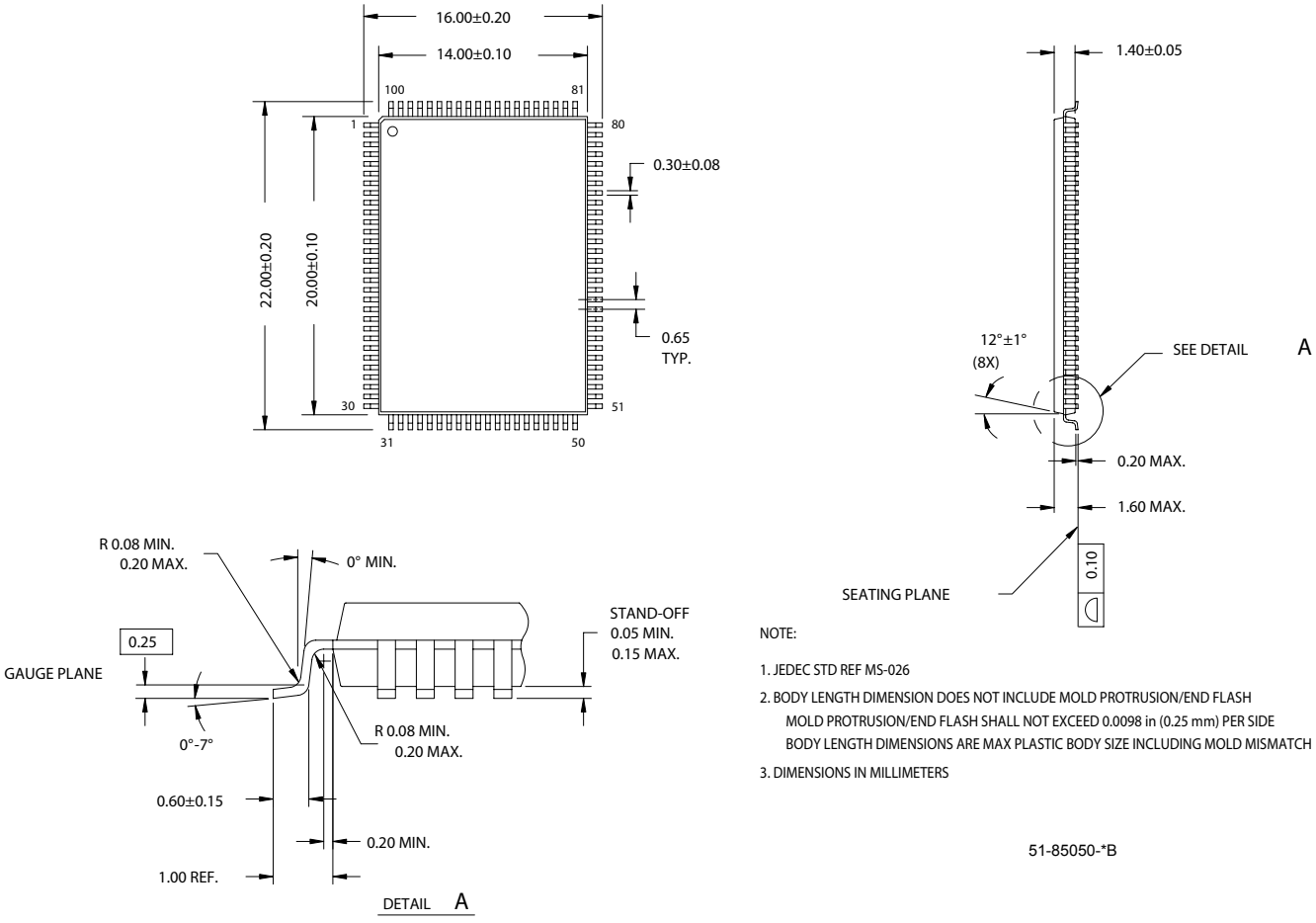
Ordering Information

Not all of the speed, package, and temperature ranges are available. Please contact your local sales representative or visit www.cypress.com for actual products offered.

Speed (MHz)	Ordering Code	Package Diagram	Part and Package Type	Operating Range
133	CY7C1381DV25-133AXC	51-85050	100-Pin Thin Quad Flat Pack (14 x 20 x 1.4 mm) Pb-Free	Commercial
	CY7C1383DV25-133AXC			
	CY7C1381FV25-133BGC	51-85115	119-ball Ball Grid Array (14 x 22 x 2.4 mm)	
	CY7C1383FV25-133BGC			
	CY7C1381FV25-133BGXC	51-85115	119-ball Ball Grid Array (14 x 22 x 2.4 mm) Pb-Free	
	CY7C1383FV25-133BGXC			
	CY7C1381DV25-133BZC	51-85180	165-ball Fine-Pitch Ball Grid Array (13 x 15 x 1.4 mm)	
	CY7C1383DV25-133BZC			
	CY7C1381DV25-133BZXC	51-85180	165-ball Fine-Pitch Ball Grid Array (13 x 15 x 1.4 mm) Pb-Free	
	CY7C1383DV25-133BZXC			
	CY7C1381DV25-133AXI	51-85050	100-Pin Thin Quad Flat Pack (14 x 20 x 1.4 mm) Pb-Free	Industrial
	CY7C1383DV25-133AXI			
	CY7C1381FV25-133BGI	51-85115	119-ball Ball Grid Array (14 x 22 x 2.4 mm)	
	CY7C1383FV25-133BGI			
	CY7C1381FV25-133BGXI	51-85115	119-ball Ball Grid Array (14 x 22 x 2.4 mm) Pb-Free	
	CY7C1383FV25-133BGXI			
	CY7C1381DV25-133BZI	51-85180	165-ball Fine-Pitch Ball Grid Array (13 x 15 x 1.4 mm)	
	CY7C1383DV25-133BZI			
	CY7C1381DV25-133BZXI	51-85180	165-ball Fine-Pitch Ball Grid Array (13 x 15 x 1.4 mm) Pb-Free	
	CY7C1383DV25-133BZXI			
100	CY7C1381DV25-100AXC	51-85050	100-Pin Thin Quad Flat Pack (14 x 20 x 1.4 mm) Pb-Free	Commercial
	CY7C1383DV25-100AXC			
	CY7C1381FV25-100BGC	51-85115	119-ball Ball Grid Array (14 x 22 x 2.4 mm)	
	CY7C1383FV25-100BGC			
	CY7C1381FV25-100BGXC	51-85115	119-ball Ball Grid Array (14 x 22 x 2.4 mm) Pb-Free	
	CY7C1383FV25-100BGXC			
	CY7C1381DV25-100BZC	51-85180	165-ball Fine-Pitch Ball Grid Array (13 x 15 x 1.4 mm)	
	CY7C1383DV25-100BZC			
	CY7C1381DV25-100BZXC	51-85180	165-ball Fine-Pitch Ball Grid Array (13 x 15 x 1.4 mm) Pb-Free	
	CY7C1383DV25-100BZXC			
	CY7C1381DV25-100AXI	51-85050	100-Pin Thin Quad Flat Pack (14 x 20 x 1.4 mm) Pb-Free	Industrial
	CY7C1383DV25-100AXI			
	CY7C1381FV25-100BGI	51-85115	119-ball Ball Grid Array (14 x 22 x 2.4 mm)	
	CY7C1383FV25-100BGI			
	CY7C1381FV25-100BGXI	51-85115	119-ball Ball Grid Array (14 x 22 x 2.4 mm) Pb-Free	
	CY7C1383FV25-100BGXI			
	CY7C1381DV25-100BZI	51-85180	165-ball Fine-Pitch Ball Grid Array (13 x 15 x 1.4 mm)	
	CY7C1383DV25-100BZI			
	CY7C1381DV25-100BZXI	51-85180	165-ball Fine-Pitch Ball Grid Array (13 x 15 x 1.4 mm) Pb-Free	
	CY7C1383DV25-100BZXI			

Package Diagrams

Figure 1. 100-Pin Thin Plastic Quad Flat pack (14 x 20 x 1.4 mm) (51-85050)



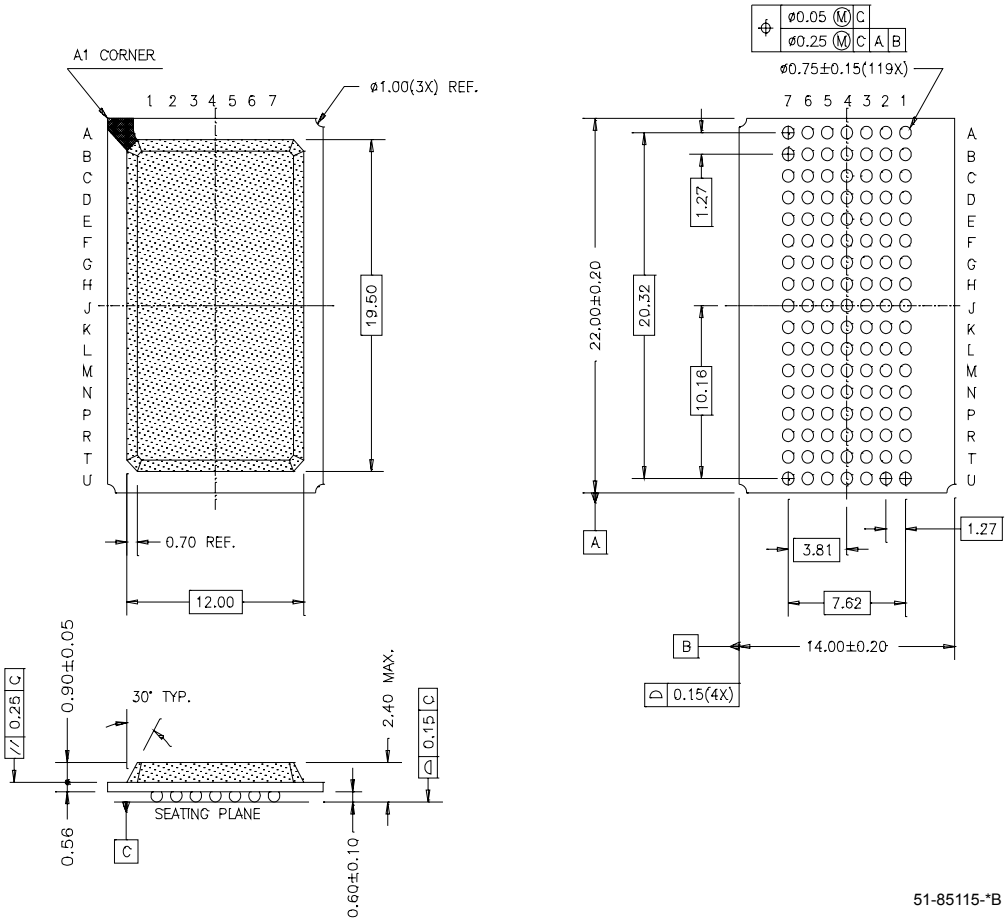
NOTE:

1. JEDEC STD REF MS-026
2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH
   MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.0098 in (0.25 mm) PER SIDE
   BODY LENGTH DIMENSIONS ARE MAX PLASTIC BODY SIZE INCLUDING MOLD MISMATCH
3. DIMENSIONS IN MILLIMETERS

51-85050-*B

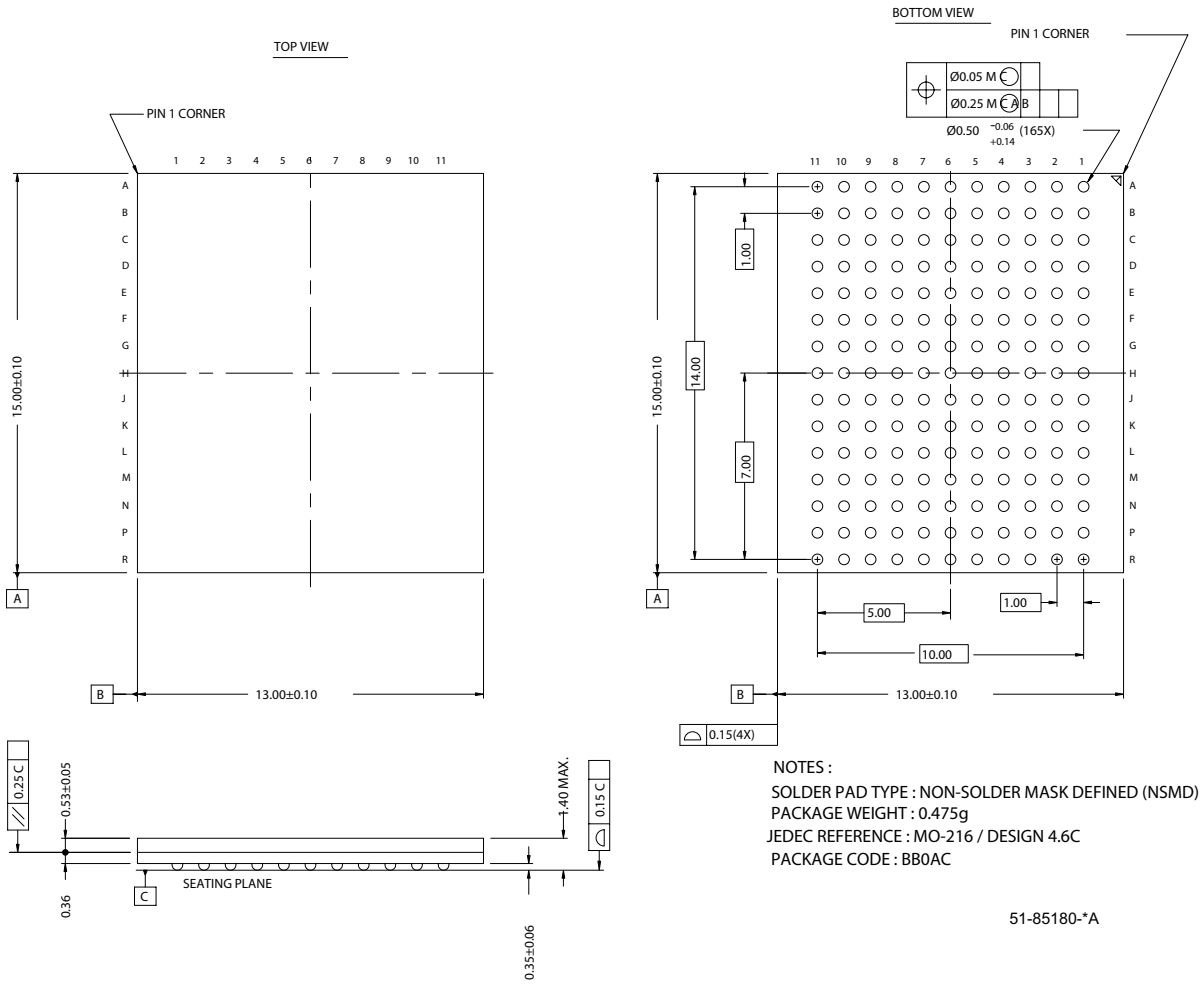
Package Diagrams (continued)

Figure 2. 119-Ball BGA (14 x 22 x 2.4 mm) (51-85115)



Package Diagrams (continued)

Figure 3. 165-Ball FBGA (13 x 15 x 1.4 mm) (51-85180)



Document History Page

Document Title: CY7C1381DV25/CY7C1383DV25/CY7C1381FV25/CY7C1383FV25, 18-Mbit (512K x 36/1M x 18) Flow-Through SRAM
Document Number: 38-05547

REV.	ECN NO.	Issue Date	Orig. of Change	Description of Change
**	254518	See ECN	RKF	New data sheet
*A	288531	See ECN	SYT	Edited description under “IEEE 1149.1 Serial Boundary Scan (JTAG)” for non-compliance with 1149.1 Removed 117Mhz Speed Bin Added Pb-free information for 100-Pin TQFP, 119 BGA and 165 FBGA Packages Added comment of ‘Pb-free BG packages availability’ below the Ordering Information
*B	326078	See ECN	PCI	Address expansion pins/balls in the pinouts for all packages are modified as per JEDEC standard Added description on EXTEST Output Bus Tri-State Changed description on the Tap Instruction Set Overview and Extest Changed Device Width (23:18) for 119-BGA from 000001 to 101001 Added separate row for 165 -FBGA Device Width (23:18) Changed Θ_{JA} and Θ_{JC} for TQFP Package from 31 and 6 °C/W to 28.66 and 4.08 °C/W respectively Changed Θ_{JA} and Θ_{Jc} or BGA Package from 45 and 7 °C/W to 23.8 and 6.2 °C/W respectively Changed Θ_{JA} and Θ_{Jc} for FBGA Package from 46 and 3 °C/W to 20.7 and 4.0 °C/W respectively Modified $V_{OL,}$ V_{OH} test conditions Removed comment of ‘Pb-free BG packages availability’ below the Ordering Information Updated Ordering Information Table
*C	416321	See ECN	NXR	Changed address of Cypress Semiconductor Corporation on Page# 1 from “3901 North First Street” to “198 Champion Court” Changed the description of I_X from Input Load Current to Input Leakage Current on page# 17 Changed the I_X current values of MODE on page # 18 from –5 μA and 30 μA to –30 μA and 5 μA Changed the I_X current values of ZZ on page # 18 from –30 μA and 5 μA to –5 μA and 30 μA Changed $V_{IH} \leq V_{DD}$ to $V_{IH} < V_{DD}$on page # 18 Replaced Package Name column with Package Diagram in the Ordering Information table
*D	475009	See ECN	VKN	Converted from Preliminary to Final. Added the Maximum Rating for Supply Voltage on V_{DDQ} Relative to GND Changed t_{TH}, t_{TL} from 25 ns to 20 ns and t_{TDOV} from 5 ns to 10 ns in TAP AC Switching Characteristics table. Updated the Ordering Information table.
*E	793579	See ECN	VKN	Added Part numbers CY7C1381FV25 and CY7C1383FV25 Added footnote# 3 regarding Chip Enable Updated Ordering Information table